Amendments to the Specification:

Please replace paragraph [0002] with the following amended paragraph:

[0002] In recent years, extensive studies have been made on techniques in which laser annealing is performed on a non-single crystal semiconductor film (an amorphous semiconductor film which is not a single crystal, or a semiconductor film having crystallinity such as a polycrystalline and microcrystalline, and a semiconductor film in which these ~~cristallinities~~ crystallinities are mixed) formed on an insulating substrate such as glass, to ~~crystalize~~ crystallize the film or to improve its crystallinity. A silicon film is often used for the above semiconductor film.

Please replace paragraph [0024] with the following amended paragraph:

[0024] However, in an industrially applicable cylindrical [[lense]] lens group, several, several tens at most, cylindrical lenses are used in consideration of its precision, cost, etc. In the cylindrical lens group as such, a laser beam is processed into a laser beam having an irregular energy distribution due to a sectional shape of the entered laser beam and the condition of entrance.

Please replace paragraph [0029] with the following amended paragraph:

[0029] In Fig. 4a, the laser beam is not entered over the entire width of the cylindrical [[lense]] lens in a cylindrical lens 4031 on the top and a cylindrical lens 4036 on the bottom. In addition, the entered beam shape is irregular.

Please replace paragraph [0043] with the following amended paragraph:

[0043] Then, the laser beam enters to an optical system for dividing this rectangular laser beam, here, the cylindrical lens group 603. For the slit 610, glass, quartz ground glass, ceramic, metal, etc. may be used, and particularly preferred is ~~lightshielding~~ light-shielding with the quartz ground glass. This is because quartz is not decomposed by the laser beam, and hardly produces substances harmful to semiconductor manufacture.

Please replace paragraph [0082] with the following amended paragraph:

[0082] Fig. 10 is a case where an [[Xecl]] XeCl excimer laser having a wave length of 308 nm is processed into a linear laser beam having a width of 500 μm extending in right-and-left direction of a paper surface, and this laser beam is irradiated on the amorphous silicon film.

Please replace paragraph [0181] with the following amended paragraph:

[0181] The divided laser beams are overlapped on the processed surface 1309 by a cylindrical lens 1306 with respect to the X-axis direction, and are overlapped on the ~~precessed~~ processed surface 1309 with respect to the Y-axis direction by a cylindrical lens 1304.

Please replace paragraph [0197] with the following amended paragraph:

[0197] The laser annealing step carried out in the above condition has effects to completely ~~crystalize~~ crystallize an amorphous region remaining after thermal crystallization, and to reduce defects or the like of a crystalline region which is already

crystallized. Thus, this step may be called a step of improving crystallinity of a semiconductor film by light annealing or a step of promoting crystallization of a semiconductor film. Such effects can also be obtained by optimizing the condition of laser annealing. In this embodiment, such a condition is called a first annealing condition.

Please replace paragraph [0257] with the following amended paragraph:

[0257] Further, one of the features of the present invention is that the p-channel TFT 3301 is formed in a self-aligning manner, and the n-channel TFTs 3302 to 3304 are formed in a ~~nonselfaligning~~ non-self-aligning manner.

Please replace the paragraph beginning at page 59, line 15, with the following amended paragraph:

[~~Fig. 2~~ Figs. 2A-2C] Views schematically showing Fig. 1.

Please replace the paragraph beginning at page 59, line 18, with the following amended paragraph:

[~~Fig. 4~~ Figs. 4A-4B] Views showing laser beams entering into the conventional optical system in which laser beam is divided.

Please replace the paragraph beginning at page 59, line 30, with the following amended paragraph:

[~~Fig. 9~~ Figs. 9A-9C] Sectional views of the energy distributions of linear laser beams in the width directions.

Please replace the paragraphs at page 60, lines 8-13, with the following amended paragraph:

[~~Fig. 15~~ Figs. 15A-15F] Views showing manufacturing steps of a pixel circuit and a control circuit.

[~~Fig. 16~~ Figs. 16A-16F] Views showing manufacturing steps of a pixel circuit and a control circuit.

[~~Fig. 17~~ Figs. 17A-17C] Views showing manufacturing steps of a pixel circuit and a control circuit.

Please replace the paragraphs at page 60, lines 24-27, with the following amended paragraph:

[~~Fig. 23~~ Figs. 23A-23F] Views showing examples of electronic equipments to which the present invention is applied.

[~~Fig. 24~~ Figs. 24A-24D] Views showing examples of projectors to which the present invention is applied.